

under the entire region of the crosspiece-shaped conductor pattern greater than the thickness of the gate insulating film directly under the main gate electrode.

Sub. B  
2. (Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a thickness of an insulating film provided on a surface of a first conductivity type semiconductor region positioned at an interface between that first conductivity type body contact region and a second conductivity type source and drain regions is made greater than the thickness of a gate insulating film directly under a gate electrode, said gate electrode being provided on the region except for said body contact region.

3. (Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a buried insulating film thicker than the thickness of the gate insulating film directly under a gate electrode is provided on a surface of a first conductivity type semiconductor region positioned at an interface between that first conductivity type body contact region and a second conductivity type source and drain regions, said gate electrode being provided on the region except for said body contact region.

4. (Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation

insulating film, wherein a gate electrode of a shape of either one of an L-shape or asymmetric T-shape comprised of a trunk-shaped main gate electrode and a crosspiece-shaped conductor pattern is provided and a body contact region and one of a source region and drain region are isolated through said crosspiece-shaped conductor pattern, said body contact region being made the same potential as one of said source region and drain region.

5. (Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a gate electrode of a shape of either one of an L-shape or asymmetric T-shape comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode is provided and at least part of said crosspiece-shaped conductor pattern functions as an effective gate electrode.